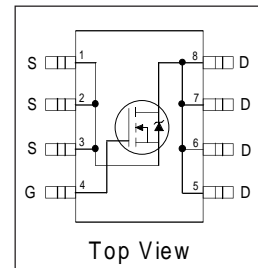


- N-Channel Application-Specific MOSFETs
- Ideal for CPU Core DC-DC Converters
- New **CopperStrap™** Interconnect for Lower Electrical and Thermal Resistance
- Low Conduction Losses
- Low Switching Losses
- Minimizes Parallel MOSFETs for high current applications

## HEXFET® Chipset for DC-DC Converters



### Description

These new devices employ advanced HEXFET® Power MOSFET technology to achieve an unprecedented balance of on-resistance and gate charge. The reduced conduction and switching losses make them ideal for high efficiency DC-DC converters that power the latest generation of mobile microprocessors.

The IRF7809/IRF7811 employs a new **CopperStrap™** interconnect technology pioneered by International Rectifier to dramatically improve the electrical & thermal resistance contribution of the package. The new **CopperStrap** SO-8 power MOSFETs are capable of current ratings over 17A and power dissipation of 3.5W @ 25°C ambient conditions, thereby reducing the need for paralleled devices, improving efficiency and reliability and reducing board space.

### DEVICE RATINGS

	IRF7809	IRF7811
$V_{DS}$	30V	28V
$R_{DS(on)}$	7.5 mΩ	11 mΩ
$Q_G$	77.5 nC	23 nC
$Q_{sw}$	23.9 nC	7 nC
$Q_{oss}$	30 nC	31 nC

### Absolute Maximum Ratings

Parameter	Symbol	IRF7809	IRF7811	Units
Drain-Source Voltage	$V_{DS}$	30	28	V
Gate-Source Voltage	$V_{GS}$	±12		
Continuous Drain or Source Current ( $V_{GS} \geq 4.5V$ )	$T_A = 25^\circ C$	17.6	14	A
	$T_L = 90^\circ C$	16.3	13	
Pulsed Drain Current①	$I_{DM}$	100	100	
Power Dissipation	$T_A = 25^\circ C$	3.5		W
	$T_L = 90^\circ C$	3.0		
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 150		°C
Continuous Source Current (Body Diode)	$I_S$	2.5	2.5	A
Pulsed Source Current①	$I_{SM}$	50	50	

### Thermal Resistance

Parameter		Max.	Units
Maximum Junction-to-Ambient③	$R_{\theta JA}$	35	°C/W
Maximum Junction-to-Lead	$R_{\theta JL}$	20	°C/W

# IRF7809/IRF7811

International  
**IR** Rectifier

Electrical Characteristics		IRF7809			IRF7811			Units	Conditions
Parameter		Min	Typ	Max	Min	Typ	Max		
Drain-to-Source Breakdown Voltage*	$BV_{DSS}$	30	-	-	28	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Static Drain-Source on Resistance*	$R_{DS(on)}$		6	7.5		9	11	m $\Omega$	$V_{GS} = 4.5V, I_D = 15A$ ②
Gate Threshold Voltage*	$V_{GS(th)}$	1.0			1.0			V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Drain-Source Leakage Current*	$I_{DSS}$			30			30	$\mu A$	$V_{DS} = 24V, V_{GS} = 0$
				150			150		$V_{DS} = 24V, V_{GS} = 0,$ $T_j = 100^\circ C$
Gate-Source Leakage Current*	$I_{GSS}$			$\pm 100$			$\pm 100$	nA	$V_{GS} = \pm 12V$
Total Gate Chg Cont FET*	$Q_G$		66.7	86.6		19	23	nC	$V_{GS} = 5V, I_D = 15A, V_{DS} = 16V$
Total Gate Chg Sync FET*	$Q_G$		59.6	77.5		17	20.5		$V_{GS} = 5V, V_{DS} < 100mV$
Pre-Vth Gate-Source Charge	$Q_{GS1}$		14			2.7			$V_{DS} = 16V, I_D = 15A$
Post-Vth Gate-Source Charge	$Q_{GS2}$		4			1.3			
Gate to Drain Charge	$Q_{GD}$		12.2			4.5			
Switch Chg( $Q_{GS2} + Q_{GD}$ )*	$Q_{sw}$		18.4	24		5.8	7.0		
Output Charge*	$Q_{oss}$		25	30		26	31		$V_{DS} = 16V, V_{GS} = 0$
Gate Resistance	$R_G$		1.5			1.9		$\Omega$	
Turn-on Delay Time	$t_{d(on)}$		17			10		ns	$V_{DD} = 16V, I_D = 15A$ $V_{GS} = 5V$ Clamped Inductive Load
Rise Time	$t_r$		10			5			
Turn-off Delay Time	$t_{d(off)}$		39			19			
Fall Time	$t_f$		19			8			
Input Capacitance	$C_{iss}$	-	7300	-	-	1800	-	pF	$V_{DS} = 16V, V_{GS} = 0$
Output Capacitance	$C_{oss}$	-	900	-	-	900	-		
Reverse Transfer Capacitance	$C_{rss}$	-	350	-	-	60	-		

## Source-Drain Rating & Characteristics

Parameter		Min	Typ	Max	Min	Typ	Max	Units	Conditions
Diode Forward Voltage*	$V_{SD}$			1.0			1.0	V	$I_S = 15A$ ②, $V_{GS} = 0V$
Reverse Recovery Charge④	$Q_{rr}$		94			82		nC	$V_{DS} = 16V, V_{GS} = 0V, I_S = 15A$
Reverse Recovery Charge (with Parallel Schottky)④	$Q_{rr(s)}$		87			74			$V_{DS} = 16V, V_{GS} = 0V, I_S = 15A$

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
  - ② Pulse width  $\leq 300 \mu s$ ; duty cycle  $\leq 2\%$ .
  - ③ When mounted on 1 inch square copper board,  $t < 10$  sec.
  - ④ Typ = measured -  $Q_{oss}$
- \* Devices are 100% tested to these parameters.

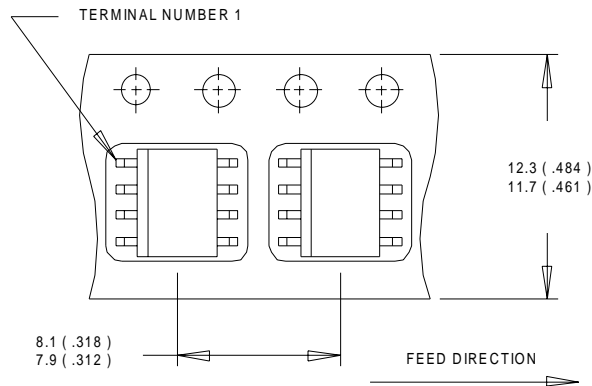


# IRF7809/IRF7811

International  
**IR** Rectifier

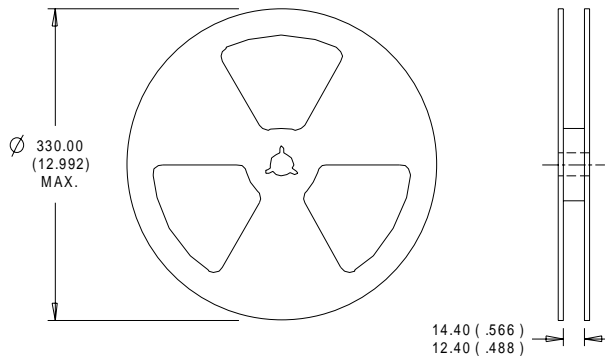
## SO-8 Tape & Reel Information

Dimensions are shown in millimeters (inches)



### NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



### NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

International  
**IR** Rectifier

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<http://www.irf.com/> Data and specifications subject to change without notice. 1/00